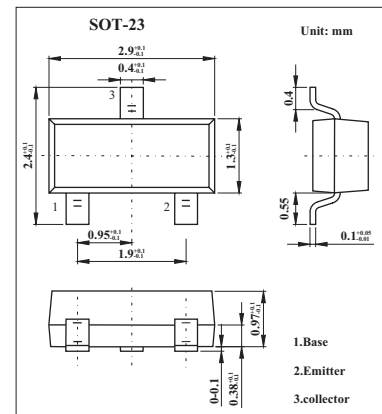


Silicon NPN Epitaxial

2SC2618

■ Features

- Low frequency amplifier.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	35	V
Collector-emitter voltage	V _{CEO}	35	V
Emitter-base voltage	V _{EBO}	4	V
Collector current	I _C	500	mA
Collector dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA , I _E = 0	35			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA , R _{BE} = ∞	35			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = 10μA , I _C = 0	4			V
Collector cutoff current	I _{CBO}	V _{CB} = 20V , I _C = 0			0.5	μA
DC current gain	h _{FE1}	V _{CE} = 3V , I _C = 10mA	100		320	
	h _{FE2}	V _{CE} = 3V , I _C = 500mA	10			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 150mA , I _B = 15mA		0.2	0.6	V
Base-emitter voltage	V _{BE}	V _{CE} = 3V , I _C = 10mA		0.64		V

■ hFE Classification

Marking	RC	RD
hFE	100~200	160~320